

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSII)

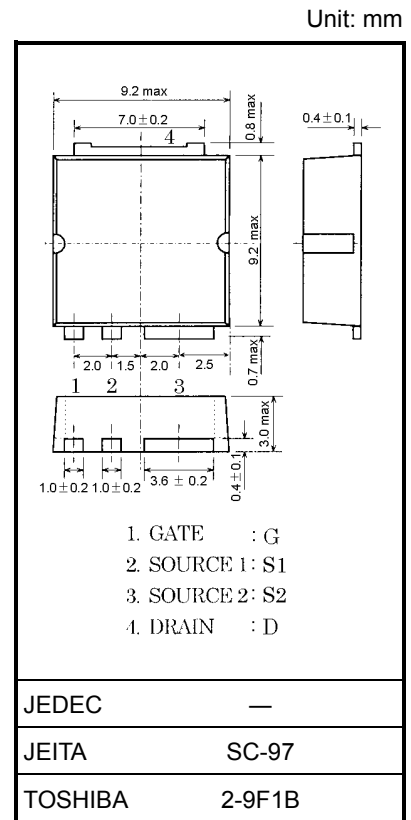
## 2SK3442

Switching Regulator, DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 15 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 28 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \text{ }\mu\text{A}$  ( $V_{DS} = 100 \text{ V}$ )
- Enhancement-mode:  $V_{th} = 2.0\sim 4.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	100	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	100	V
Gate-source voltage		$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	45	A
	Pulse (Note 1)	$I_{DP}$	180	
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )		$P_D$	125	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	468	mJ
Avalanche current		$I_{AR}$	45	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	12.5	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	$-55\sim 150$	$^\circ\text{C}$



Weight: 0.74 g (typ.)

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.00	$^\circ\text{C/W}$

Note 1: Please use devices on condition that the channel temperature is below  $150^\circ\text{C}$ .

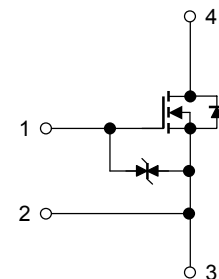
Note 2:  $V_{DD} = 25 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 373 \text{ }\mu\text{H}$ ,  $R_G = 25 \text{ }\Omega$ ,  $I_{AR} = 45 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

#### Notice:

Please use the S1 pin for gate input signal return. Make sure that the main current flows into S2 pin.



## Electrical Characteristics (Note 4) (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	100	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 23\text{ A}$	—	15	20	$\text{m}\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 23\text{ A}$	14	28	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	4100	—	pF
Reverse transfer capacitance		$C_{rss}$		—	340	—	
Output capacitance		$C_{oss}$		—	980	—	
Switching time	Rise time	$t_r$		—	15	—	ns
	Turn-on time	$t_{on}$		—	45	—	
	Fall time	$t_f$		—	20	—	
	Turn-off time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10\ \mu\text{s}$	—	95	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 80\text{ V}, V_{GS} = 10\text{ V}, I_D = 45\text{ A}$	—	85	—	nC
Gate-source charge		$Q_{gs}$		—	50	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	35	—	

Note 4: Please connect the S1 pin and S2 pin, and then ground the connected pin.  
(However, while switching times are measured, please don't connect and ground it.)

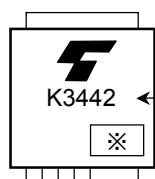
## Source-Drain Ratings and Characteristics (Note 5) (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1, Note 5)	$I_{DR1}$	—	—	—	45	A
Pulse drain reverse current (Note 1, Note 5)	$I_{DRP1}$	—	—	—	180	A
Continuous drain reverse current (Note 1, Note 5)	$I_{DR2}$	—	—	—	1	A
Pulse drain reverse current (Note 1, Note 5)	$I_{DRP2}$	—	—	—	4	A
Forward voltage (diode)	$V_{DS2F}$	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.5	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V},$	—	160	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	512	—	nC

Note 5:  $I_{DR1}, I_{DRP1}$ : drain, flowing current value between the S2 pin, open the S1 pin  
 $I_{DR2}, I_{DRP2}$ : drain, flowing current value between the S1 pin, open the S2 pin

Unless otherwise specified, please connect the S1 and S2 pins, and then ground the connected pin.

## Marking

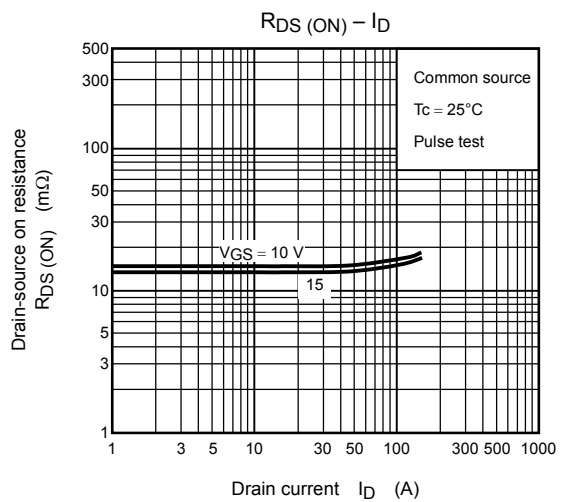
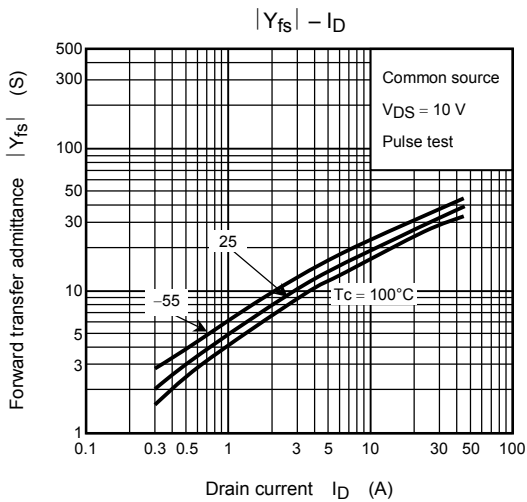
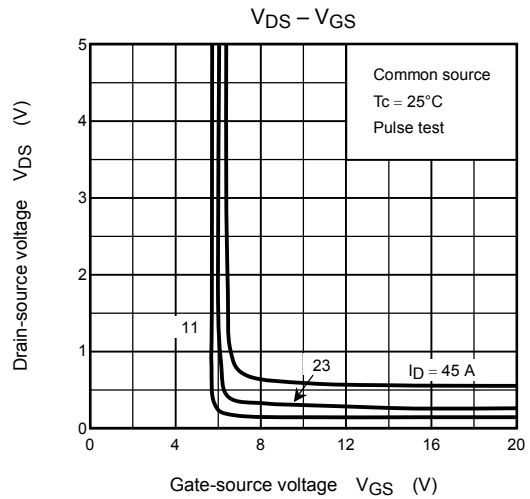
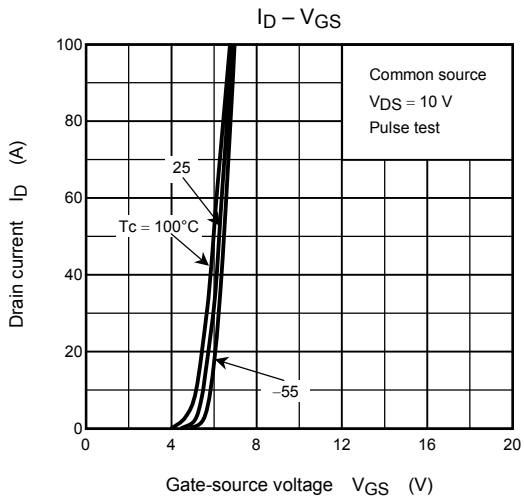
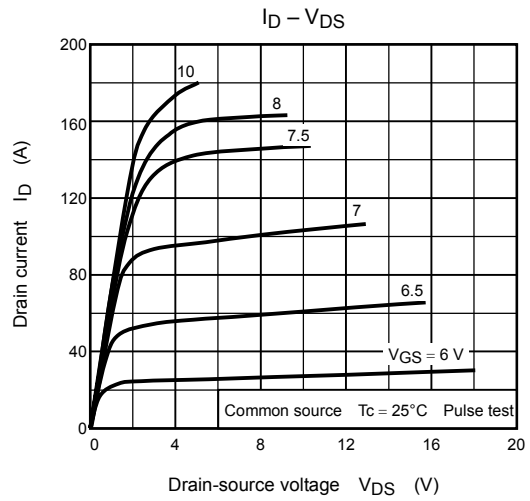
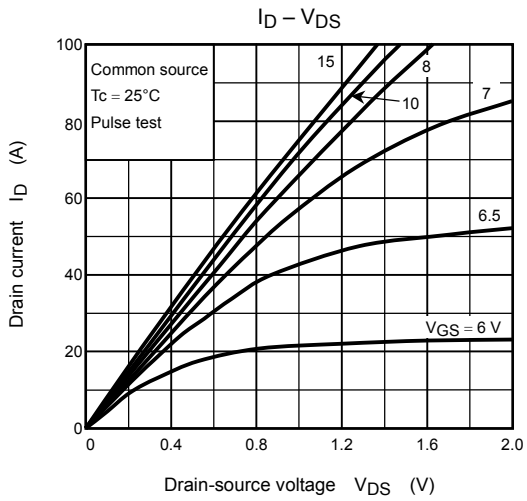


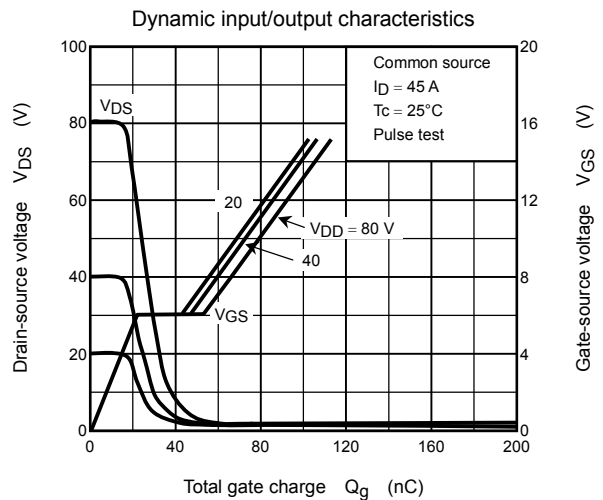
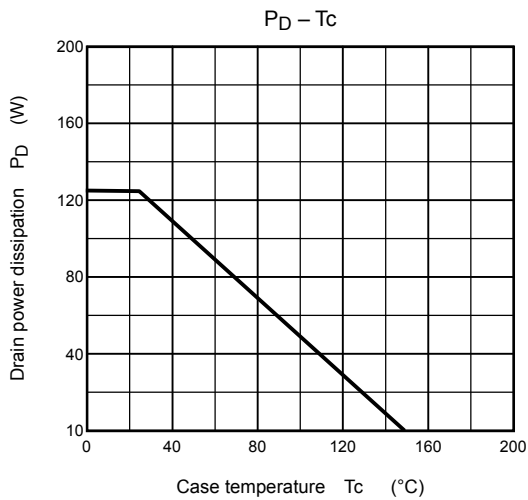
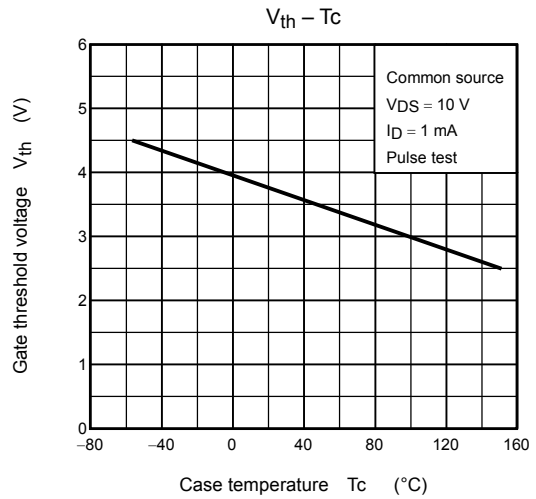
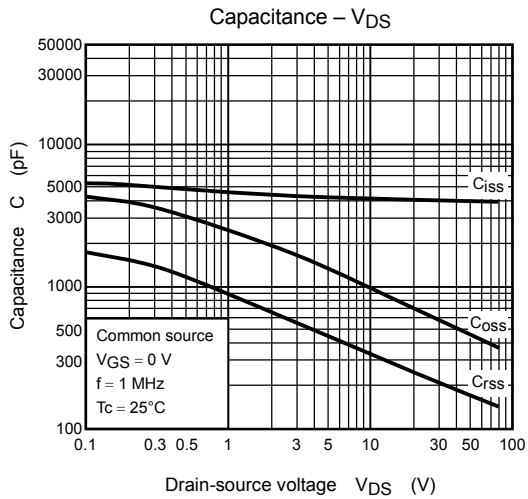
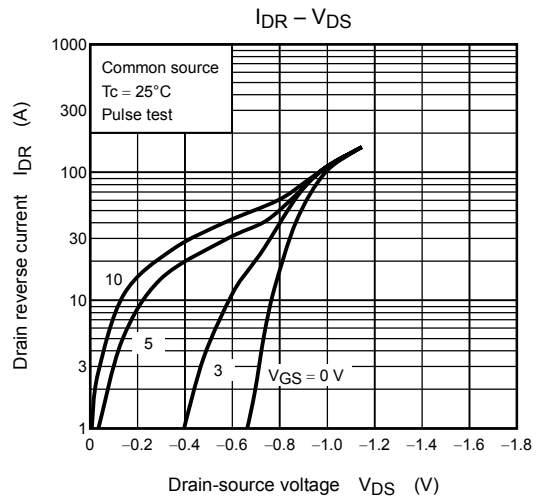
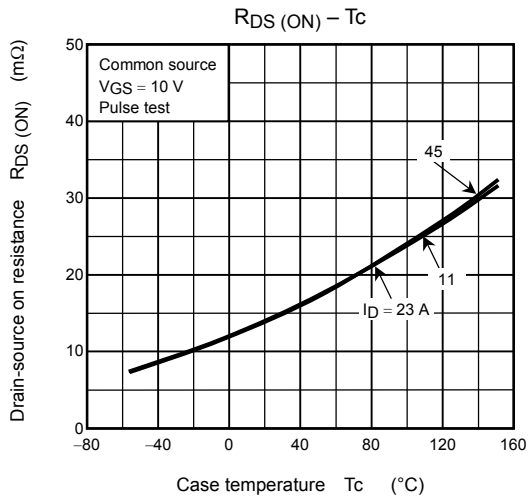
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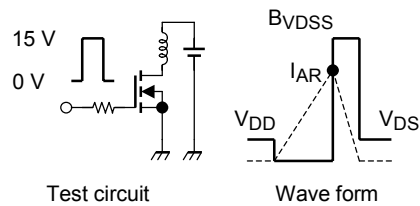
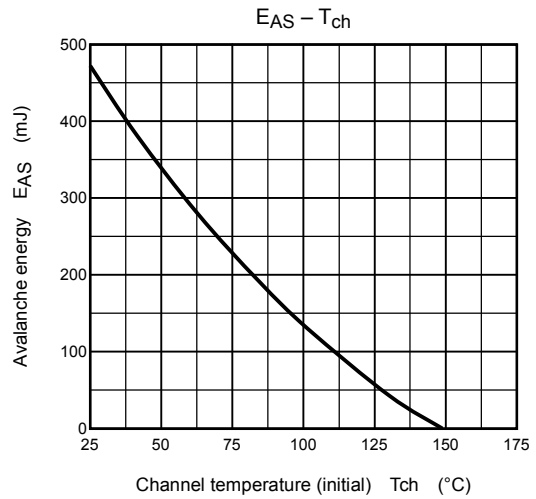
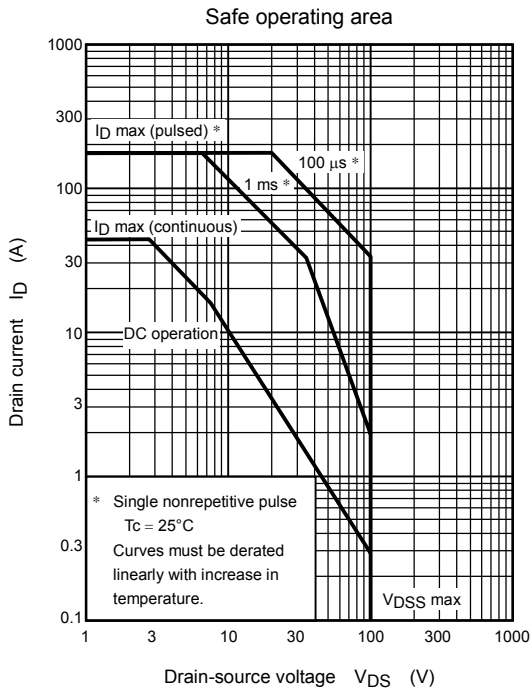
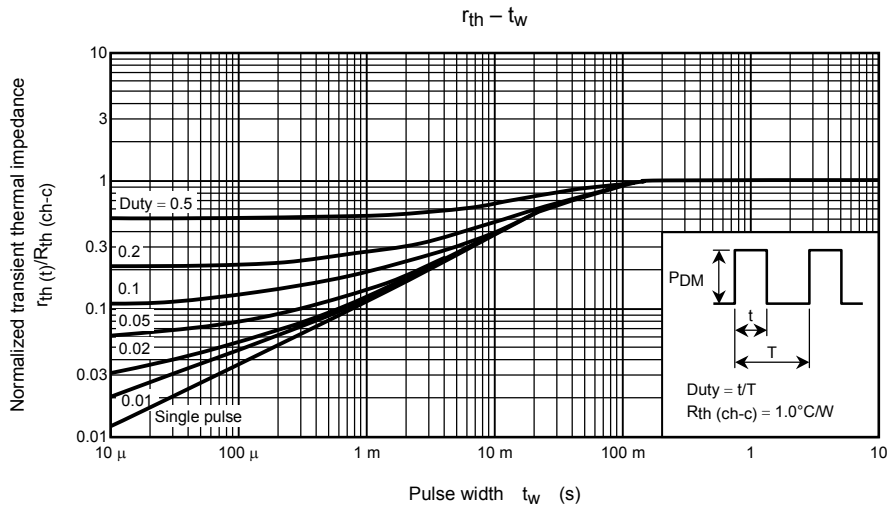
※ Lot Number

Month (starting from alphabet A)

Year (last number of the christian era)







$$R_G = 25 \Omega$$

$$V_{DD} = 25 V, L = 373 \mu H$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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